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P A T E N T & T R A D E M A R K S C B

PTO/SB/08 Equivalent

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Multiple sheets used when necessary)</i>		Application No.	10/661,414
		Filing Date	September 12, 2003
		First Named Inventor	Gonzalez
		Art Unit	2826
SHEET 1 OF 1		Examiner	Fetsum Abraham
		Attorney Docket No.	MICRON.079DV1C1

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
PT		5,101,251	03-31-1992	Wakamiya, et al.	
PT		5,395,786	03-07-1995	Hsu, et al.	
PT		5,658,811	08-19-1997	Kimura, et al.	
PT		5,668,035	09-16-1997	Fang, et al.	
PT		5,731,238	03-24-1998	Cavins, et al.	
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PT		6,136,728	10-24-2000	Wang	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
PT		Sekine et al., "Self-aligned tungsten strapped source/drain and gate technology realizing the lowest sheet resistance for sub-quarter micron CMOS," International Electron Devices Meeting, December 1994, IEEE, p. 493-496	

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Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	<i>5/2/05</i>
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

T¹ - Place a check mark in this area when an English language Translation is attached.